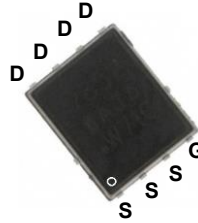
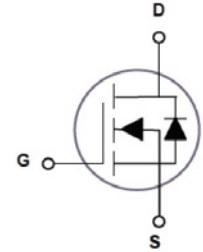


Main Product Characteristics

$V_{(BR)DSS}$	40V
$R_{DS(ON)}$	1.4m Ω
I_D	200A



PPAK 5x6



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The SSFP4998 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current – Continuous ($T_C=25^\circ\text{C}$)	I_D	200	A
Drain Current – Continuous ($T_C=100^\circ\text{C}$)		130	A
Drain Current – Pulsed ¹	I_{DM}	800	A
Single Pulse Avalanche Energy ²	E_{AS}	450	mJ
Single Pulse Avalanche Current ²	I_{AS}	30	A
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	92.6	W
Power Dissipation – Derate above 25°C		0.74	W/ $^\circ\text{C}$
Storage Temperature Range	T_{STG}	-50 to +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-50 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	---	62	$^\circ\text{C/W}$
Thermal Resistance Junction to Case	$R_{\theta JC}$	---	1.35	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40	---	---	V
		V _{DS} =40V, V _{GS} =0V, T _J =25°C	---	---	1	uA
Drain-Source Leakage Current	I _{DSS}	V _{DS} =32V, V _{GS} =0V, T _J =125°C	---	---	10	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
On Characteristics						
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =50A	---	1.1	1.4	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	1	---	3	V
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =50A	---	120	---	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3, 4}	Q _g	V _{DS} =20V, V _{GS} =10V, I _D =50A	---	115	200	nC
Gate-Source Charge ^{3, 4}	Q _{gs}		---	24	40	
Gate-Drain Charge ^{3, 4}	Q _{gd}		---	19	36	
Turn-On Delay Time ^{3, 4}	T _{d(on)}	V _{DD} =20V, V _{GS} =10V, R _G =3Ω, I _D =50A	---	20	48	nS
Rise Time ^{3, 4}	T _r		---	32	68	
Turn-Off Delay Time ^{3, 4}	T _{d(off)}		---	98	200	
Fall Time ^{3, 4}	T _f		---	32	70	
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1MHz	---	7500	12000	pF
Output Capacitance	C _{oss}		---	230	460	
Reverse Transfer Capacitance	C _{rss}		---	3.2	10	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	1.4	2.8	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I _S		---	---	200	A
Pulsed Source Current	I _{SM}	V _G =V _D =0V, Force Current	---	---	800	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =50A, di/dt=100A/μS	---	64	---	ns
Reverse Recovery Charge	Q _{rr}	T _J =25°C	---	98	---	nC

Note:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=1mH, I_{AS}=30A, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300uS, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

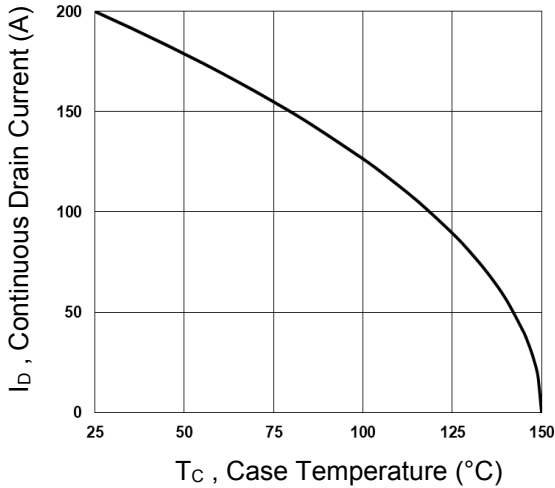


Fig.1 Continuous Drain Current vs. T_c

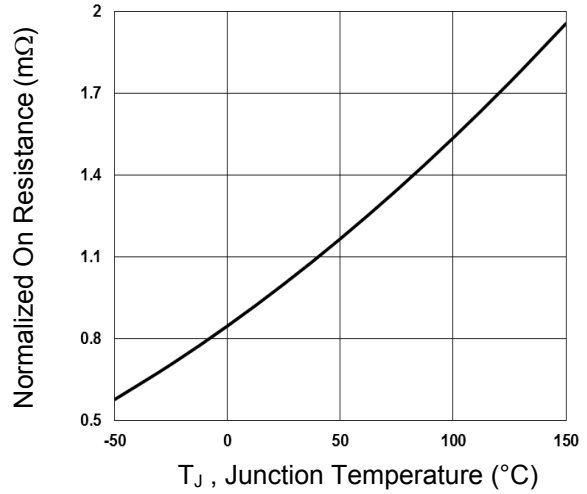


Fig.2 Normalized $R_{DS(ON)}$ vs. T_J

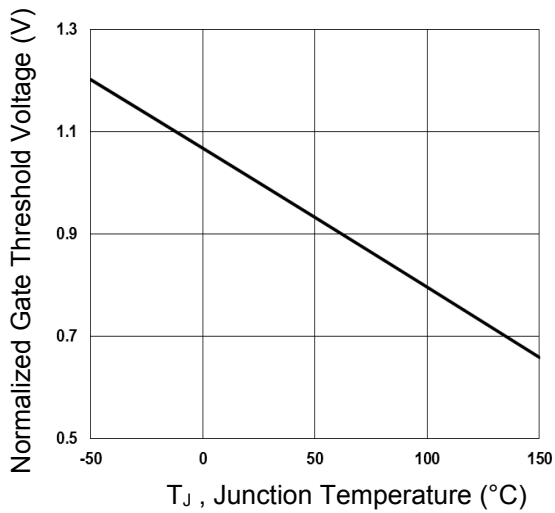


Fig.3 Normalized V_{th} vs. T_J

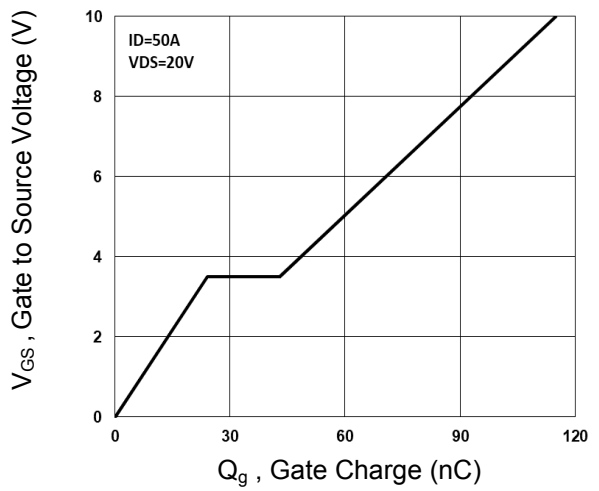


Fig.4 Gate Charge Characteristics

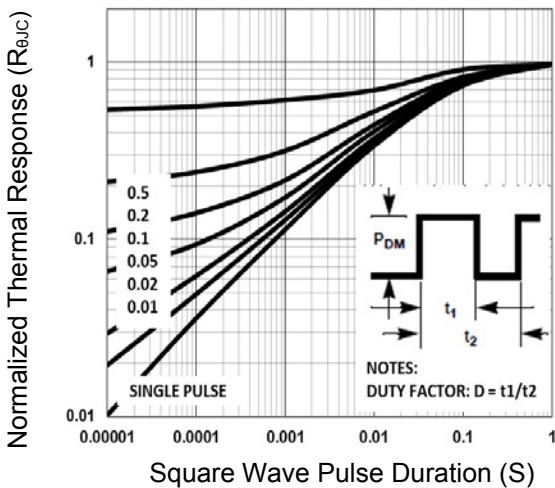


Fig.5 Normalized Transient Impedance

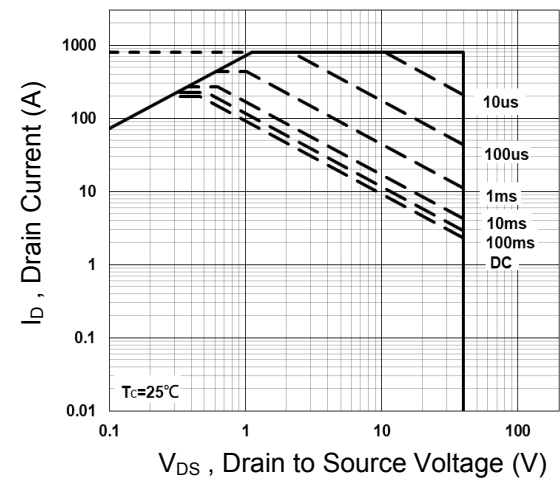


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

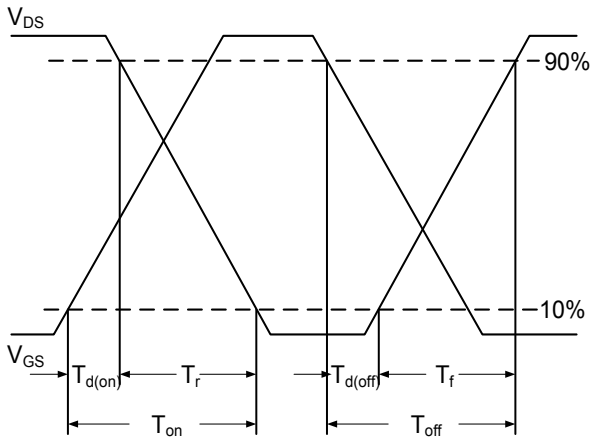


Fig.7 Switching Time Waveform

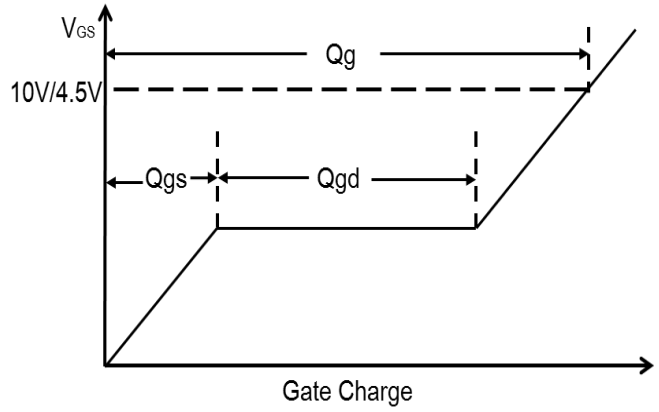
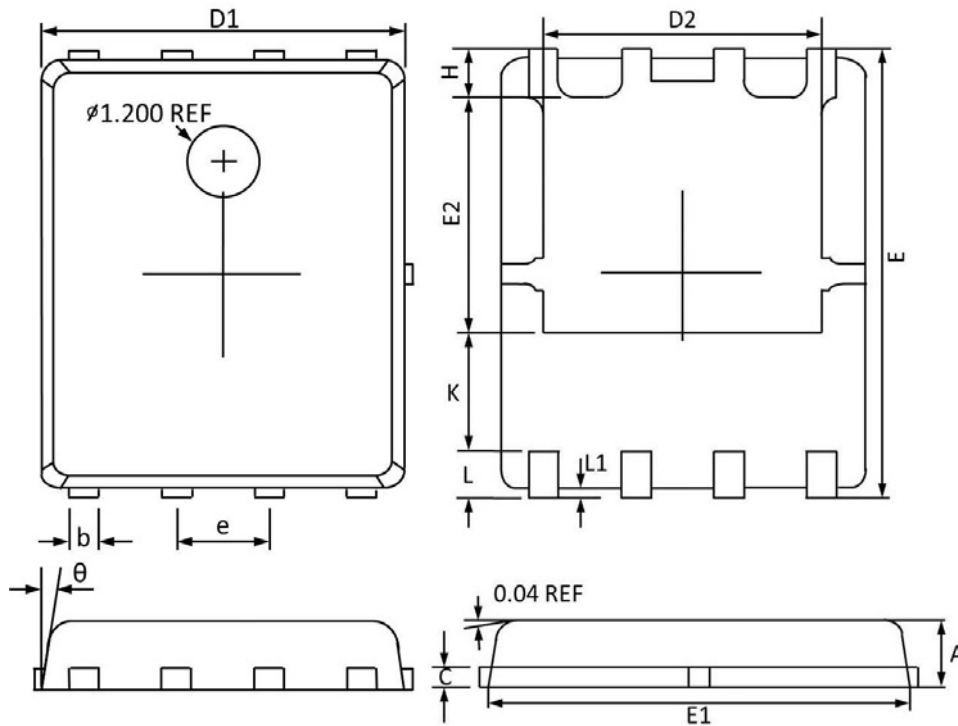


Fig.8 Gate Charge Waveform

Package Outline Dimensions PPAK5x6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
b	0.510	0.330	0.020	0.013
C	0.300	0.200	0.012	0.008
D1	5.100	4.800	0.201	0.189
D2	4.100	3.610	0.161	0.142
E	6.200	5.900	0.244	0.232
E1	5.900	5.700	0.232	0.224
E2	3.780	3.350	0.149	0.132
e	1.27BSC		0.05BSC	
H	0.700	0.410	0.028	0.016
K	1.500	1.100	0.059	0.043
L	0.710	0.510	0.028	0.020
L1	0.200	0.060	0.008	0.002
θ	12°	0°	12°	0°